

In the Claims:

1. (Currently Amended) A method of manufacturing a module, the method comprising:
providing a device that includes a connection area extending over a top surface of the device, wherein the connection area comprises a compliant 3D structure;
applying a casting compound over the top surface of the device ~~so that the connection area protrudes through the casting compound;~~
after applying a casting compound, reducing a thickness of the casting compound so that the connection area protrudes through the casting compound; and
after applying a casting compound, electrically coupling the connection area to a terminal of a second apparatus.
2. (Original) The method of claim 1 wherein the second apparatus comprises a printed circuit board, the method further comprising, after applying the casting compound, mounting the module to the printed circuit board.
3. (Original) The method of claim 1 wherein the second apparatus comprises a lead frame, the method further comprising, after forming the casting compound, attaching the module to the lead frame.
4. (Original) The method of claim 1 wherein electrically coupling the connection area comprises soldering the connection area to the terminal.

5. (Currently Amended) The method of claim 1 wherein the ~~connection area is formed over~~ a compliant 3D structure comprises a compliant base element, on which an electrically conductive structure of metal is applied.
6. (Currently Amended) The method of claim 1 wherein the ~~connection area~~ compliant 3D structure ~~comprises at least one of a solder ball, a μ spring or a soft bump.~~
7. (Original) The method of claim 1 wherein the device comprises a semiconductor wafer.
8. (Original) The method of claim 7 and further comprising separating the wafer into a plurality of individual chips, wherein the casting compound is applied to the wafer before the separating.
9. (Original) The method of claim 8 wherein separation corridors between the chips on the wafer are exposed before the separating.
10. (Original) The method of claim 9 wherein the separation corridors are exposed by a photolithographic process.
11. (Original) The method of claim 9 wherein the separation corridors are exposed with use of a laser beam.
12. (Original) The method of claim 8 wherein the wafer is cooled to a temperature at which the casting compound is adequately brittle before separating the wafer into a plurality of individual chips.

13. (Original) The method of claim 1 wherein the casting compound is applied uniformly by spraying, dispensing or printing.
14. (Original) The method of claim 1 wherein the casting compound has thermal and mechanical properties comparable to those of silicon.
15. (Original) The method of claim 14 wherein the casting compound comprises a silicon-based material.
16. (Original) The method of claim 14 wherein the casting compound comprises a thermoplastic material.
17. (Original) The method of claim 14 wherein the casting compound comprises an epoxy resin.
18. (Canceled).
19. (Currently Amended) The method of claim ~~[[18]]~~ 1 wherein the thickness of the casting compound is reduced by thermal removal.
20. (Currently Amended) The method of claim ~~[[18]]~~ 1 wherein the thickness of the casting compound is reduced by etching.
21. (Currently Amended) A method for improving the mechanical properties of a BOC module arrangement in which chips have 3D structures which are mechanically and electrically connected by means of solder connections to terminal contacts on a printed circuit board or

leadframe, the method characterized in that a casting compound is applied over the top surface of the device, and excess thickness of the casting compound is removed, provided for the chips in such a way that tips of the 3D structures protrude from the compound, wherein the 3D structures comprise compliant 3D structures.

22. (Currently Amended) The method of claim 21 wherein the compliant 3D structure comprises structures comprise a structure selected from the group consisting of solder balls, μ springs.

23. (Currently Amended) The method of claim 21 wherein the compliant 3D structures comprises compliant 3D structures and soft bumps structure comprises a compliant base element, on which an electrically conductive structure of metal is applied.

24. (Original) The method of claim 21 wherein the chips comprise a plurality of chips on a semiconductor wafer.

25. (Original) The method of claim 21 wherein the chips comprise individual semiconductor dies.